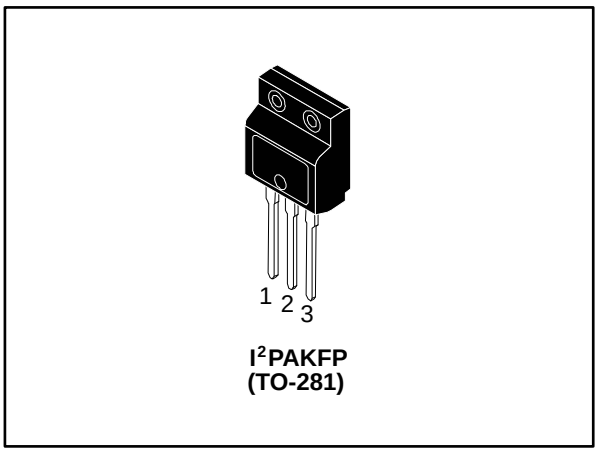
# STFI10LN80K5

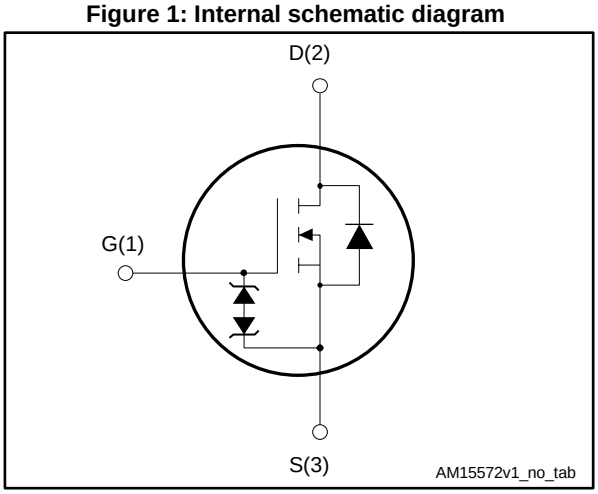
## N-channel 800 V, 0.55 Ω typ., 8 A MDmesh™ K5 Power MOSFET in a I²PAKFP package

Datasheet - production data




**I²PAKFP (TO-281)**

**Figure 1: Internal schematic diagram**




## Features

| Order code | $V_{DS}$ | $R_{DS(on)}$ max. | $I_D$ |
|---|---|---|---|
| STFI10LN80K5 | 800 V | 0.63 Ω | 8 A |

- Fully insulated and low profile package with increased creepage path from pin to heatsink plate
- Industry's $R_{DS(on)}$ x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

**Table 1: Device summary**

| Order code | Marking | Package | Packing |
|---|---|---|---|
| STFI10LN80K5 | 10LN80K5 | I²PAKFP | Tube |

# Contents

# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $V_{GS}$ | Gate-source voltage | ± 30 | V |
| $I_D$ (1) | Drain current (continuous) at $T_C$ = 25 °C | 8 | A |
| $I_D$ (1) | Drain current (continuous) at $T_C$ = 100 °C | 5 | A |
| $I_D$ (2) | Drain current pulsed | 32 | A |
| $P_{TOT}$ | Total dissipation at $T_C$ = 25 °C | 20 | W |
| $V_{ISO}$ | Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; $T_C$=25°C) | 2500 | V |
| dv/dt (3) | Peak diode recovery voltage slope | 4.5 | V/ns |
| dv/dt (4) | MOSFET dv/dt ruggedness | 50 | |
| $T_j$ | Operating junction temperature range | - 55 to 150 | °C |
| $T_{stg}$ | Storage temperature range | | |

**Notes:**

(1)Limited by maximum junction temperature.

(2)Pulse width limited by safe operating area

(3)$I_{SD}$≤ 8 A, di/dt≤100 A/µs; $V_{DS}$ peak ≤ $V_{(BR)DSS}$

(4)$V_{DS}$ ≤ 640 V

**Table 3: Thermal data**

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $R_{thj\text{-}case}$ | Thermal resistance junction-case | 6.25 | °C/W |
| $R_{thj\text{-}amb}$ | Thermal resistance junction-ambient | 62.5 | °C/W |

**Table 4: Avalanche characteristics**

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $I_{AR}$ | Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$) | 2.7 | A |
| $E_{AS}$ | Single pulse avalanche energy (starting $T_j$ = 25 °C, $I_D$ = $I_{AR}$, $V_{DD}$ = 50 V) | 240 | mJ |

# 2 Electrical characteristics

$T_C$ = 25 °C unless otherwise specified

**Table 5: On/off-state**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS}$ = 0 V, $I_D$ = 1 mA | 800 | | | V |
| $I_{DSS}$ | Zero gate voltage drain current | $V_{GS}$ = 0 V, $V_{DS}$ = 800 V | | | 1 | µA |
| | | $V_{GS}$ = 0 V, $V_{DS}$ = 800 V $T_C$ = 125 °C (1) | | | 50 | µA |
| $I_{GSS}$ | Gate body leakage current | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | ±10 | µA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 100 µA | 3 | 4 | 5 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS}$ = 10 V, $I_D$ = 4 A | | 0.55 | 0.63 | Ω |

**Notes:**

(1)Defined by design, not subject to production test.

**Table 6: Dynamic**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $C_{iss}$ | Input capacitance | $V_{DS}$ = 100 V, f = 1 MHz, $V_{GS}$ = 0 V | - | 427 | - | pF |
| $C_{oss}$ | Output capacitance | | - | 43 | - | pF |
| $C_{rss}$ | Reverse transfer capacitance | | - | 0.25 | - | pF |
| $C_{o(tr)}$ (1) | Equivalent capacitance time related | $V_{DS}$ = 0 to 640 V, $V_{GS}$ = 0 V | - | 72 | - | pF |
| $C_{o(er)}$ (2) | Equivalent capacitance energy related | | | 27 | - | pF |
| $R_g$ | Intrinsic gate resistance | f = 1 MHz , $I_D$= 0 A | - | 7 | - | Ω |
| $Q_g$ | Total gate charge | $V_{DD}$ = 640 V, $I_D$ = 8 A $V_{GS}$= 10 V (see *Figure 16: "Test circuit for gate charge behavior"*) | - | 15 | - | nC |
| $Q_{gs}$ | Gate-source charge | | - | 4.2 | - | nC |
| $Q_{gd}$ | Gate-drain charge | | - | 9 | - | nC |

**Notes:**

(1)Time related is defined as a constant equivalent capacitance giving the same charging time as $C_{oss}$ when $V_{DS}$ increases from 0 to 80% $V_{DSS}$

(2)Energy related is defined as a constant equivalent capacitance giving the same stored energy as $C_{oss}$ when $V_{DS}$ increases from 0 to 80% $V_{DSS}$

**Table 7: Switching times**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD}$= 400 V, $I_D$ = 4 A, $R_G$ = 4.7 Ω $V_{GS}$ = 10 V (see *Figure 15: "Test circuit for resistive load switching times"* and *Figure 20: "Switching time waveform"*) | - | 11.8 | - | ns |
| $t_r$ | Rise time | | - | 10 | - | ns |
| $t_{d(off)}$ | Turn-off delay time | | - | 28 | - | ns |
| $t_f$ | Fall time | | - | 13 | - | ns |

**Table 8: Source-drain diode**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $I_{SD}$ | Source-drain current | | - | | 8 | A |
| $I_{SDM}$ (1) | Source-drain current (pulsed) | | - | | 32 | A |
| $V_{SD}$ (2) | Forward on voltage | $I_{SD}$ = 8 A, $V_{GS}$ = 0 V | - | | 1.5 | V |
| $t_{rr}$ | Reverse recovery time | $I_{SD}$ = 8 A, di/dt = 100 A/µs, $V_{DD}$ = 60 V (see *Figure 17: "Test circuit for inductive load switching and diode recovery times"*) | - | 350 | | ns |
| $Q_{rr}$ | Reverse recovery charge | | - | 3.9 | | µC |
| $I_{RRM}$ | Reverse recovery current | | - | 22.5 | | A |
| $t_{rr}$ | Reverse recovery time | $I_{SD}$ = 8 A, di/dt = 100 A/µs, $V_{DD}$ = 60 V, $T_j$ = 150 °C (see *Figure 17: "Test circuit for inductive load switching and diode recovery times"*) | - | 505 | | ns |
| $Q_{rr}$ | Reverse recovery charge | | - | 5 | | µC |
| $I_{RRM}$ | Reverse recovery current | | - | 20 | | A |

**Notes:**

(1)Pulse width limited by safe operating area

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5%

**Table 9: Gate-source Zener diode**

| Symbol | Parameter | Test conditions | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{(BR)GSO}$ | Gate-source breakdown voltage | $I_{GS}$= ± 1 mA, $I_D$= 0 A | 30 | - | - | V |

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection,thus eliminating the need for additional external componentry.

## 2.2 Electrical characteristics (curves)

**Figure 2: Safe operating area**

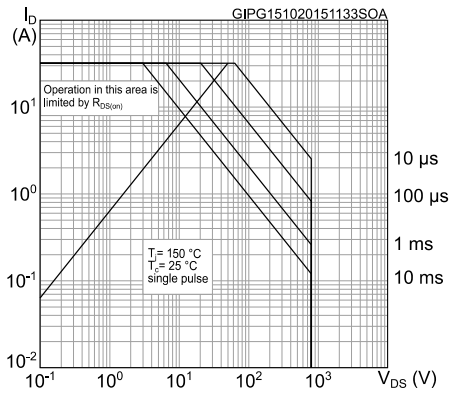



**Figure 3: Thermal impedance**

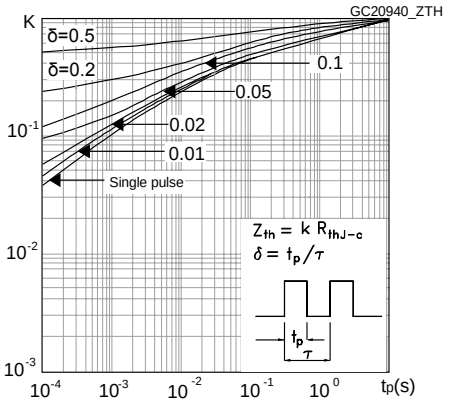



**Figure 4: Output characteristics**

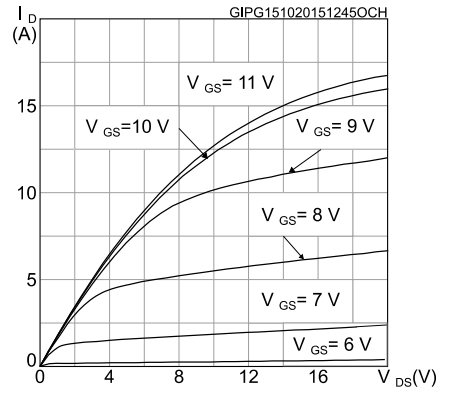



**Figure 5: Transfer characteristics**

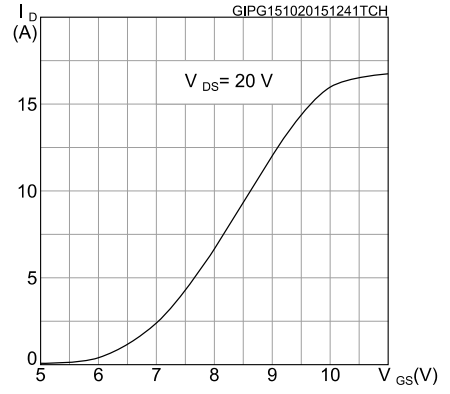



**Figure 6: Gate charge vs gate-source voltage**

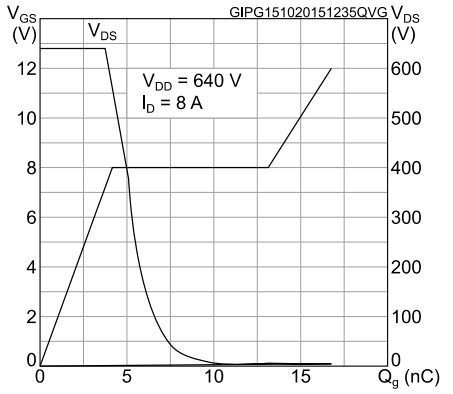



**Figure 7: Static drain-source on-resistance**

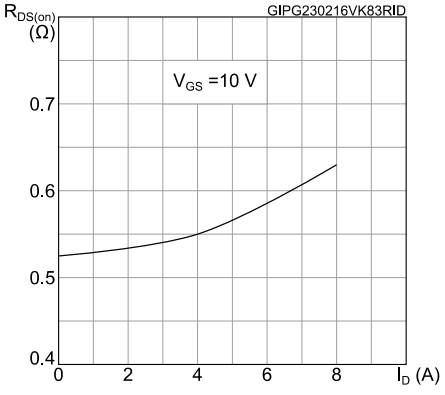


**Figure 8: Capacitance variations**

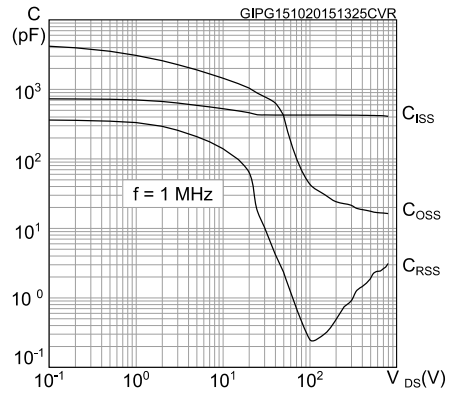



**Figure 9: Normalized gate threshold voltage vs temperature**

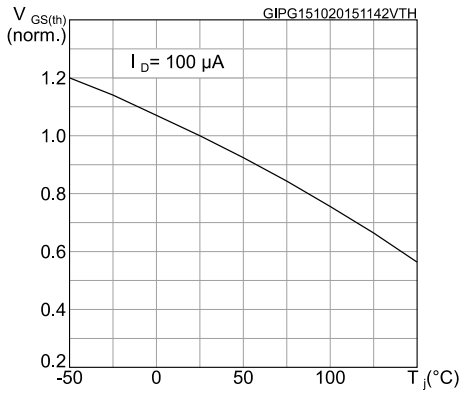



**Figure 10: Normalized on-resistance vs temperature**

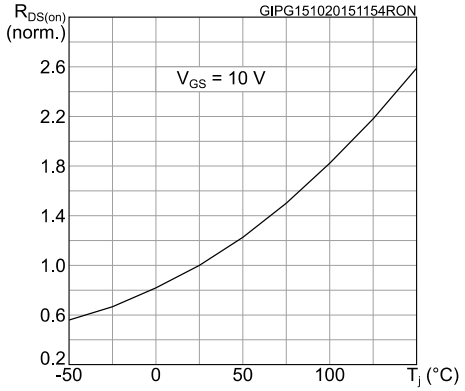



**Figure 11: Normalized $V_{(BR)DSS}$ vs temperature**

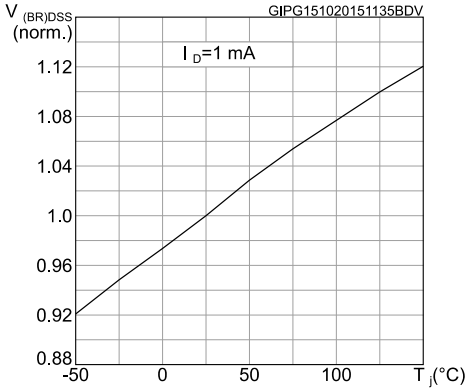



**Figure 12: Output capacitance stored energy**

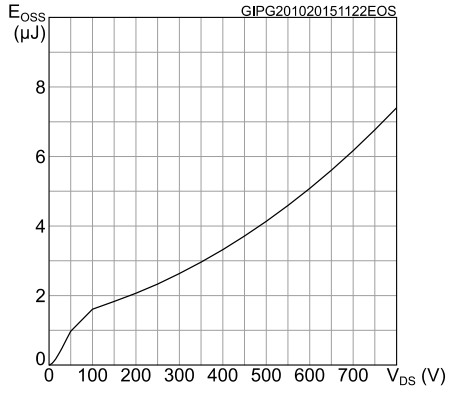



**Figure 13: Source-drain diode forward characteristics**

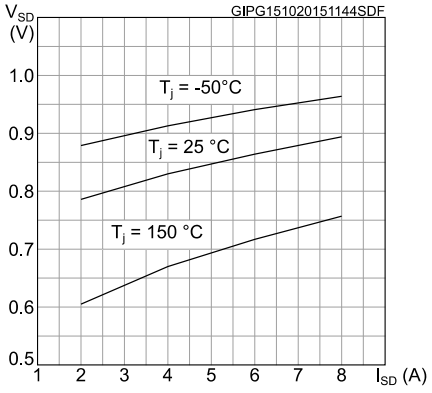
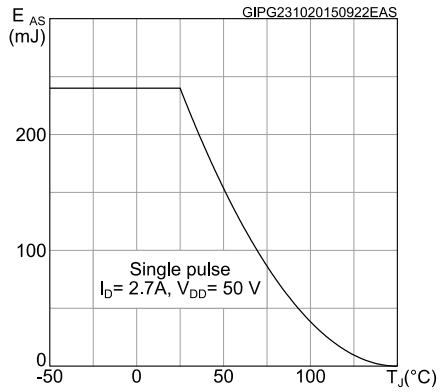


**Figure 14: Maximum avalanche energy vs starting $T_J$**



# 3 Test circuits

**Figure 15: Test circuit for resistive load switching times**

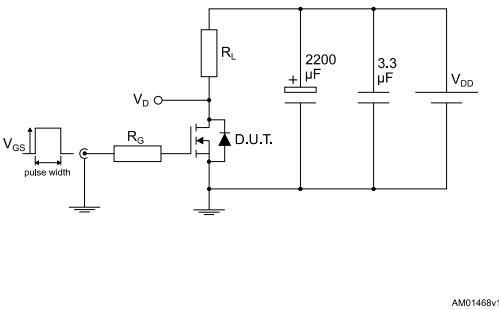



**Figure 16: Test circuit for gate charge behavior**

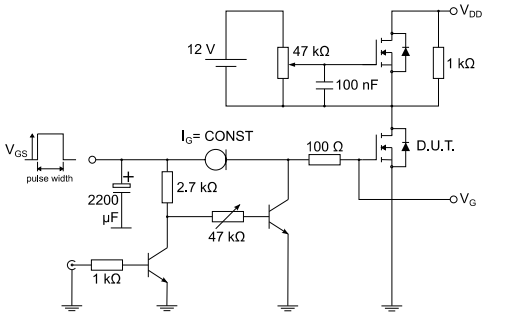



**Figure 17: Test circuit for inductive load switching and diode recovery times**

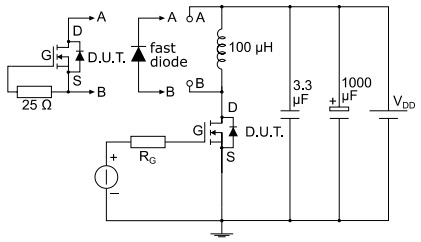



**Figure 18: Unclamped inductive load test circuit**

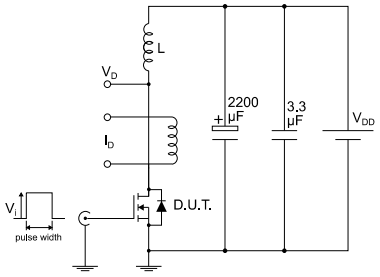



**Figure 19: Unclamped inductive waveform**

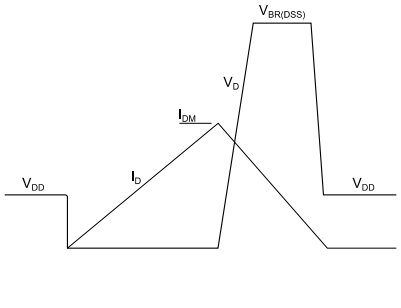
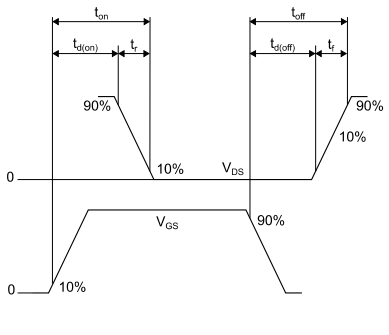



**Figure 20: Switching time waveform**



# 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

## 4.1 I²PAKFP (TO-281) package information

**Figure 21: I²PAKFP (TO-281) package outline**

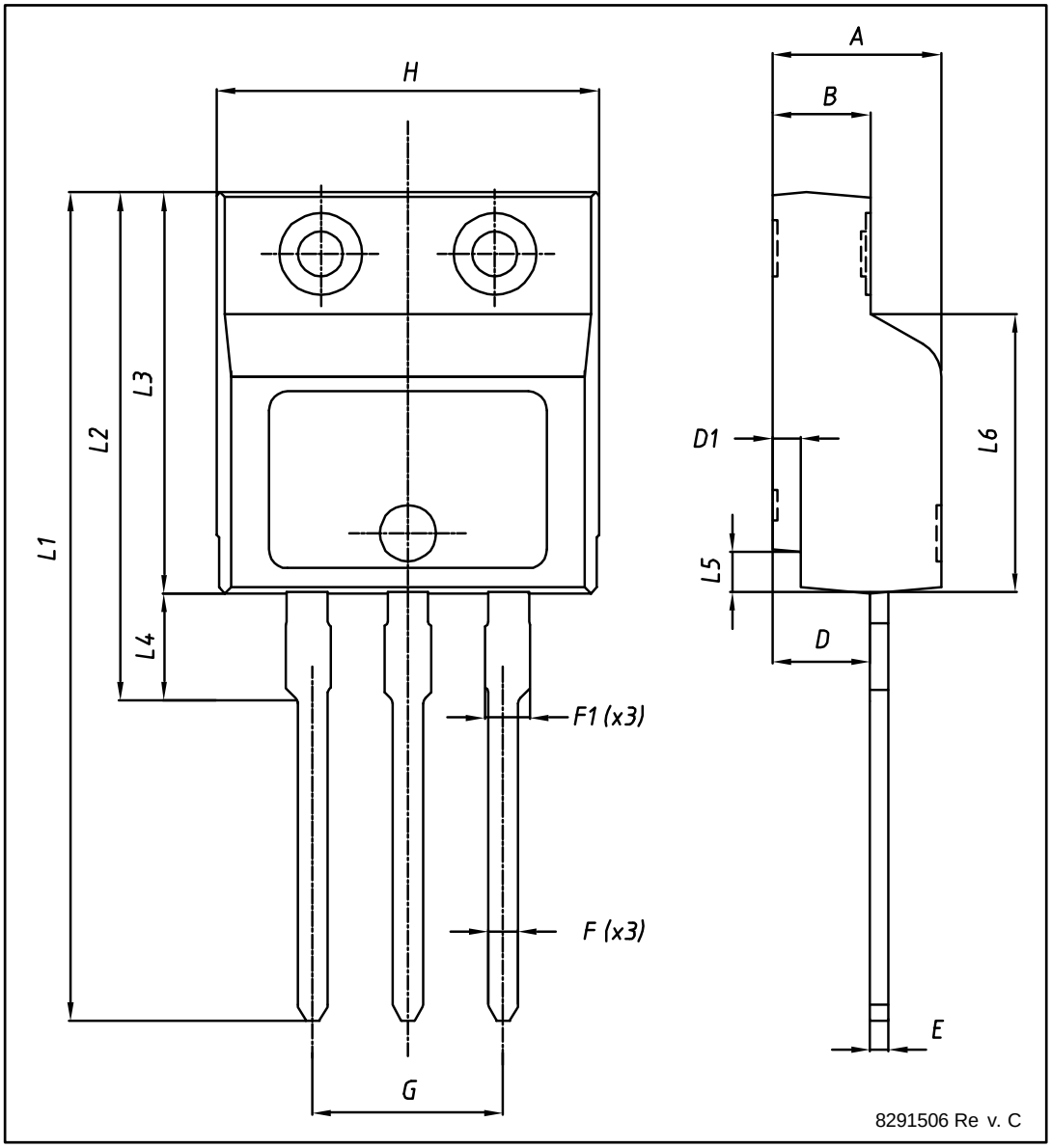


Table 10: I²PAKFP (TO-281) mechanical data

| Dim. | mm | | |
|---|---|---|---|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| B | 2.50 | | 2.70 |
| D | 2.50 | | 2.75 |
| D1 | 0.65 | | 0.85 |
| E | 0.45 | | 0.70 |
| F | 0.75 | | 1.00 |
| F1 | | | 1.20 |
| G | 4.95 | | 5.20 |
| H | 10.00 | | 10.40 |
| L1 | 21.00 | | 23.00 |
| L2 | 13.20 | | 14.10 |
| L3 | 10.55 | | 10.85 |
| L4 | 2.70 | | 3.20 |
| L5 | 0.85 | | 1.25 |
| L6 | 7.50 | 7.60 | 7.70 |

# 5 Revision history

Table 11: Document revision history

| Date | Revision | Changes |
|---|---|---|
| 10-Feb-2016 | 1 | First release. |

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